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(54) Title: INDUCTIVELY COUPLED DUAL ZONE PROCESSING CHAMBER WITH SINGLE PLANAR ANTENNA

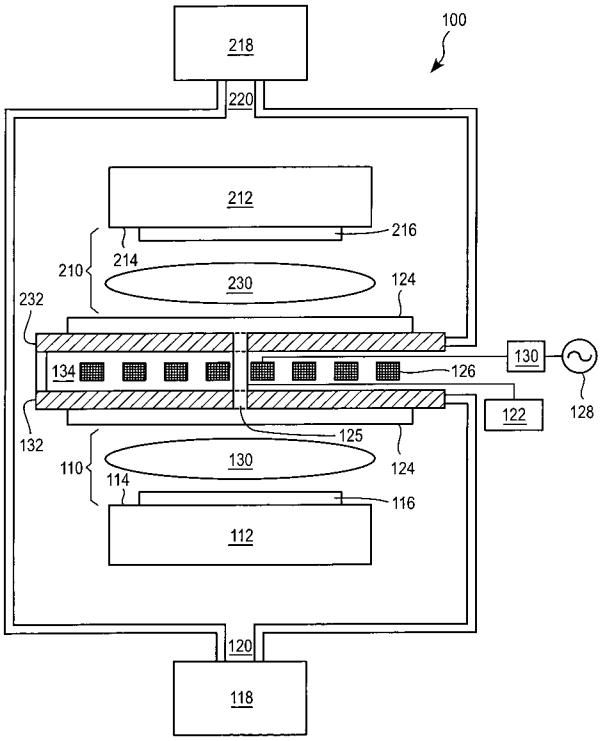


FIG. 2

(57) Abstract: A dual zone plasma processing chamber is provided. The plasma processing chamber includes a first substrate support having a first support surface adapted to support a first substrate within the processing chamber and a second substrate support having a second support surface adapted to support a second substrate within the processing chamber. One or more gas sources in fluid communication with one or more gas distribution members supply process gas to a first zone adjacent to the first substrate support and a second zone adjacent to the second substrate support. A radio-frequency (RF) antenna adapted to inductively couple RF energy into the interior of the processing chamber and energize the process gas into a plasma state in the first and second zones. The antenna is located between the first substrate support and the second substrate support.

WO 2009/005624 A3

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